

### **BIPOLAR ANALOG INTEGRATED CIRCUIT**

# $\mu$ PC3242TB

### 3.3 V, SILICON GERMANIUM MMIC WIDE BAND AMPLIFIER

#### **DESCRIPTION**

The uPC3242TB is a silicon germanium monolithic integrated circuit designed as IF amplifier for DBS LNB.

This device exhibits low noise figure and high power gain characteristics.

This IC is manufactured using our UHSK3 (<u>U</u>ltra <u>High Speed Process</u>) silicon germanium bipolar process.

#### **FEATURES**

Low current : Icc = 4.3 mA TYP.

Power gain : G<sub>P</sub> = 22 dB TYP. @ f = 1.0 GHz

: G<sub>P</sub> = 22 dB TYP. @ f = 2.2 GHz

• Gain flatness :  $\Delta G_P = 0.4 \text{ dB TYP}$ . @ f = 1.0 to 2.2 GHz

Noise figure : NF = 4.0 dB TYP. @ f = 1.0 GHz

: NF = 4.0 dB TYP. @ f = 2.2 GHz

• High linearity : Po (1 dB) = -7.5 dBm TYP. @ f = 1.0 GHz

: Po (1 dB) = -9.5 dBm TYP. @ f = 2.2 GHz

• Supply voltage : Vcc = +3.0 to +3.6 V• Port impedance : input/output 50  $\Omega$ 

#### **APPLICATIONS**

· IF amplifiers in DBS LNB, other L-band amplifiers, etc.

#### ORDERING INFORMATION

Part Number	Order Number	Package	Marking	Supplying Form
μPC3242TB-E3	μPC3242TB-E3-A	6-pin super minimold (Pb-Free)	C3Z	<ul> <li>Embossed tape 8 mm wide</li> <li>Pin 1, 2, 3 face the perforation side of the tape</li> </ul>
		(PD-Flee)		Qty 3 kpcs/reel

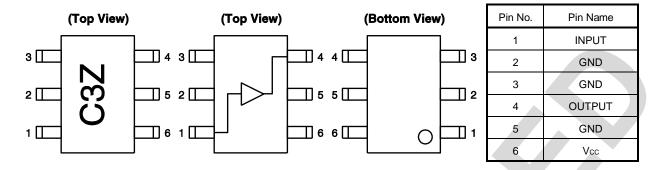
**Remark** To order evaluation samples, please contact your nearby sales office.

Part number for sample order: µPC3242TB-A

Caution: Observe precautions when handling because these devices are sensitive to electrostatic discharge

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

#### PIN CONNECTIONS AND INTERNAL BLOCK DIAGRAM



PRODUCT LINE-UP OF 5 V or 3.3 V-BIAS SILICON MMIC WIDE BAND AMPLIFIER (TA = +25°C, Vcc = +5.0 V or +3.3 V, Zs = ZL = 50  $\Omega$ )

Part No.	Vcc	Icc	G₽	NF	Po (sat)	Po (1 dB)	Package	Marking
	(V)	(mA)	(dB)	(dB)	(dBm)	(dBm)		
μPC2711TB	+5.0	12.0	13.0 (1.0 GHz)	5.0 (1.0 GHz)	+1.0 (1.0 GHz)	-	6-pin	C1G
μPC2712TB		12.0	20.0 (1.0 GHz)	4.5 (1.0 GHz)	+3.0 (1.0 GHz)	-	super	C1H
μPC3215TB		14.0	20.5 (1.5 GHz)	2.3 (1.5 GHz)	+3.5 (1.5 GHz)	+1.5 (1.5 GHz)	minimold	СЗН
μPC3224TB		9.0	21.5 (1.0 GHz)	4.3 (1.0 GHz)	+4.0 (1.0 GHz)	-3.5 (1.0 GHz)		СЗК
			21.5 (2.2 GHz)	4.3 (2.2 GHz)	+1.5 (2.2 GHz)	–5.5 (2.2 GHz)		
μPC3227TB		4.8	22.0 (1.0 GHz)	4.7 (1.0 GHz)	-1.0 (1.0 GHz)	-6.5 (1.0 GHz)		C3P
			22.0 (2.2 GHz)	4.6 (2.2 GHz)	-3.5 (2.2 GHz)	-8.0 (2.2 GHz)		
μPC3240TB	+3.3	13.0	25.0 (1.0 GHz)	4.3 (1.0 GHz)	-	+1.0 (1.0 GHz)		C3W
			24.5 (2.2 GHz)	4.5 (2.2 GHz)	_	-4.0 (2.2 GHz)		
μPC3242TB		4.3	22.0 (1.0 GHz)	4.0 (1.0 GHz)	-0.5 (1.0 GHz)	–7.5 (1.0 GHz)		C3Z
			22.0 (2.2 GHz)	4.0 (2.2 GHz)	-4.0 (2.2 GHz)	–9.5 (2.2 GHz)		

Remark Typical performance. Please refer to ELECTRICAL CHARACTERISTICS in detail.

#### **ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Conditions		Ratings	Unit
Supply Voltage	Vcc	T <sub>A</sub> = +25°C		4.0	V
Total Circuit Current	Icc	T <sub>A</sub> = +25°C		10	mA
Power Dissipation	Po	T <sub>A</sub> = +85°C	Note	270	mW
Operating Ambient Temperature	Та			-40 to +85	°C
Storage Temperature	T <sub>stg</sub>			-55 to +150	°C
Input Power	Pin	T <sub>A</sub> = +25°C		-10	dBm

**Note** Mounted on double-sided copper-clad  $50 \times 50 \times 1.6$  mm epoxy glass PWB

#### RECOMMENDED OPERATING RANGE

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Supply Voltage	Vcc		+3.0	+3.3	+3.6	V
Operating Ambient Temperature	TA		-40	+25	+85	°C

# ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = +25°C, V<sub>CC</sub> = +3.3 V, Z<sub>S</sub> = Z<sub>L</sub> = 50 $\Omega$ , unless otherwise specified)

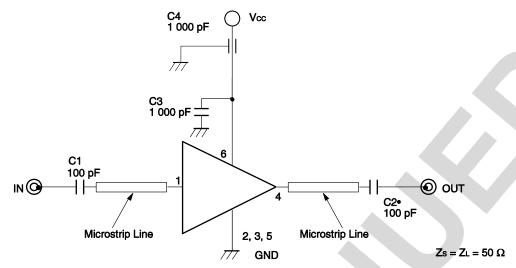
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Circuit Current	Icc	No input signal	3.6	4.3	5.0	mA
Power Gain 1	G <sub>P</sub> 1	f = 0.25 GHz, Pin = -40 dBm	19	22	25	dB
Power Gain 2	G <sub>P</sub> 2	f = 1.0 GHz, Pin = -40 dBm	19	22	25	
Power Gain 3	G <sub>P</sub> 3	f = 1.8 GHz, P <sub>in</sub> = -40 dBm	19	22	25	
Power Gain 4	G <sub>P</sub> 4	f = 2.2 GHz, P <sub>in</sub> = -40 dBm	19	22	25	
Gain 1 dB Compression Output Power 1	Po (1 dB) 1	f = 1.0 GHz	-10	-7.5	-	dBm
Gain 1 dB Compression Output Power 2	Po (1 dB) 2	f = 2.2 GHz	-12.5	-9.5	_	
Noise Figure 1	NF1	f = 1.0 GHz	-	4.0	4.8	dB
Noise Figure 2	NF2	f = 2.2 GHz	-	4.0	4.8	
Isolation 1	ISL1	$f = 1.0 \text{ GHz}, P_{in} = -40 \text{ dBm}$	31	36.5	ı	dB
Isolation 2	ISL2	f = 2.2 GHz, P <sub>in</sub> = -40 dBm	34	40.5	ı	
Input Return Loss 1	RLin1	f = 1.0 GHz, Pin = -40 dBm	10	14	-	dB
Input Return Loss 2	RLin2	f = 2.2 GHz, Pin = -40 dBm	6	8.5	ı	
Output Return Loss 1	RLout1	f = 1.0 GHz, Pin = -40 dBm	8	11	ı	dB
Output Return Loss 2	RLout2	f = 2.2 GHz, Pin = -40 dBm	8	11		

#### STANDARD CHARACTERISTICS FOR REFERENCE

(T<sub>A</sub> = +25°C, V<sub>CC</sub> = +3.3 V, Z<sub>S</sub> = Z<sub>L</sub> = 50  $\Omega$ , unless otherwise specified)

Parameter	Symbol	Test Conditions	Reference Value	Unit
Power Gain 5	G <sub>P</sub> 5	f = 2.6 GHz, P <sub>in</sub> = -40 dBm	20.5	dB
Power Gain 6	G <sub>P</sub> 6	f = 3.0 GHz, Pin = -40 dBm	19	
Gain Flatness	⊿Gp	f = 1.0 to 2.2 GHz, Pin = -40 dBm	0.4	dB
Saturated Output Power 1	Po (sat) 1	f = 1.0 GHz, P <sub>in</sub> = -15 dBm	-0.5	dBm
Saturated Output Power 2	Po (sat) 2	f = 2.2 GHz, P <sub>in</sub> = -15 dBm	-4.0	
K factor 1	K1	f = 1.0 GHz, Pin = -40 dBm	2.5	_
K factor 2	K2	f = 2.2 GHz, Pin = -40 dBm	3.4	_
Output 3rd Order Intercept Point 1	OIP <sub>3</sub> 1	f1 = 1 000 MHz, f2 = 1 001 MHz	1.5	dBm
Output 3rd Order Intercept Point 2	OIP <sub>3</sub> 2	f1 = 2 200 MHz, f2 = 2 201 MHz	-0.5	
Input 3rd Order Intercept Point 1	IIP <sub>3</sub> 1	f1 = 1 000 MHz, f2 = 1 001 MHz	-20	dBm
Input 3rd Order Intercept Point 2	IIP <sub>3</sub> 2	f1 = 2 200 MHz, f2 = 2 201 MHz	-22	1
2nd Order Intermodulation Distortion	IM <sub>2</sub>	f1 = 1 000 MHz, f2 = 1 001 MHz, P <sub>in</sub> = -40 dBm/tone	22	dBc
2nd Harmonics	2f <sub>0</sub>	fo = 1.0 GHz, Pin = -40 dBm	28.5	dBc

#### **TEST CIRCUIT**



The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.

# COMPONENTS OF TEST CIRCUIT FOR MEASURING ELECTRICAL CHARACTERISTICS

	Туре	Value
C1, C2	Chip Capacitor	100 pF
С3	Chip Capacitor	1 000 pF
C4	Feed-through Capacitor	1 000 pF

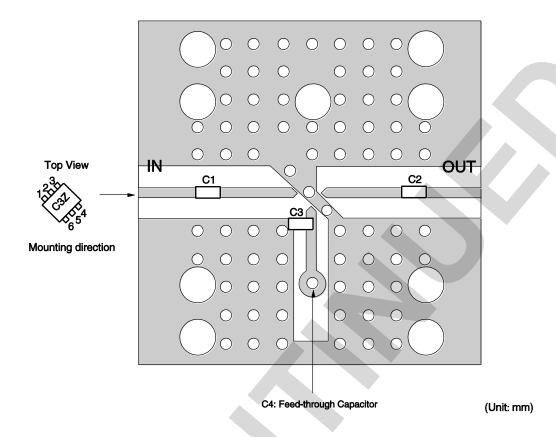
#### CAPACITORS FOR THE Vcc, INPUT AND OUTPUT PINS

Capacitors of 1 000 pF are recommendable as the bypass capacitor for the Vcc pin and the coupling capacitors for the input and output pins.

The bypass capacitor connected to the Vcc pin is used to minimize ground impedance of Vcc pin. So, stable bias can be supplied against Vcc fluctuation.

The coupling capacitors, connected to the input and output pins, are used to cut the DC and minimize RF serial impedance. Their capacitances are therefore selected as lower impedance against a 50  $\Omega$  load. The capacitors thus perform as high pass filters, suppressing low frequencies to DC.

#### ILLUSTRATION OF THE TEST CIRCUIT ASSEMBLED ON EVALUATION BOARD



#### COMPONENT LIST

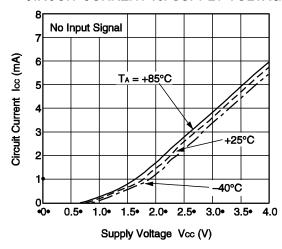
	Туре	Value	Size
C1, C2	Chip Capacitor	100 pF	1608
C3	Chip Capacitor	1 000 pF	1608
C4	Feed-through Capacitor	1 000 pF	1

#### Notes

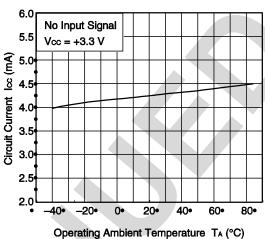
- 1.  $30 \times 30 \times 0.4$  mm double sided 35  $\mu$  m copper clad polyimide board.
- 2. Back side: GND pattern
- 3. Au plated on pattern
- 4. °○: Through holes

#### TYPICAL CHARACTERISTICS (TA = +25°C, Vcc = +3.3 V, Zs = $Z_L$ = 50 $\Omega$ , unless otherwise specified)

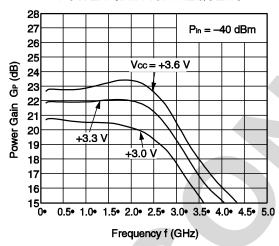
#### CIRCUIT CURRENT vs. SUPPLY VOLTAGE



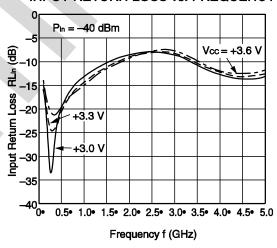
## CURCUIT CURRENT vs. OPERATING AMBIENT TEMPERATURE



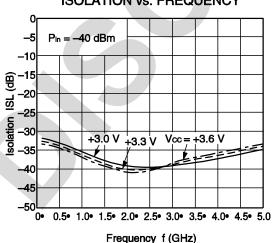
#### **POWER GAIN vs. FREQUENCY**



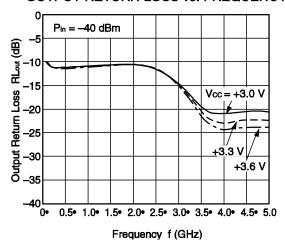
INPUT RETURN LOSS vs. FREQUENCY



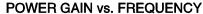
#### ISOLATION vs. FREQUENCY

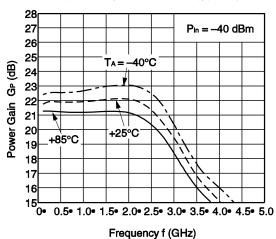


**OUTPUT RETURN LOSS vs. FREQUENCY** 

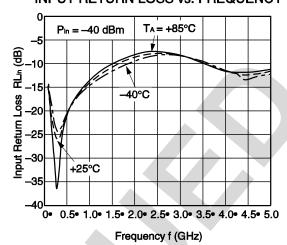


**Remark** The graphs indicate nominal characteristics.

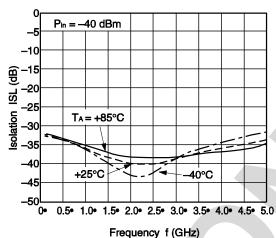




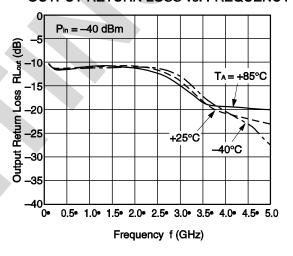
#### INPUT RETURN LOSS vs. FREQUENCY



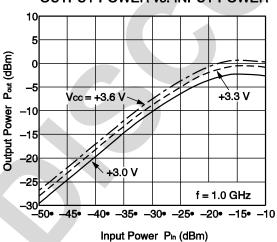
#### ISOLATION vs. FREQUENCY



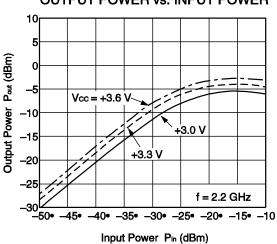
#### **OUTPUT RETURN LOSS vs. FREQUENCY**



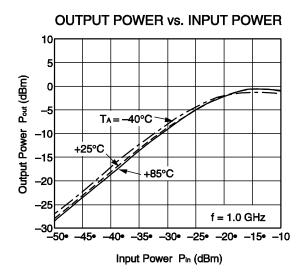
#### **OUTPUT POWER vs. INPUT POWER**

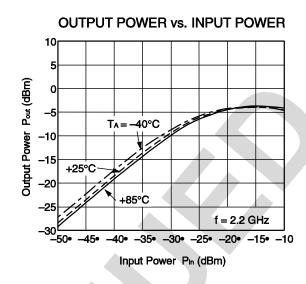


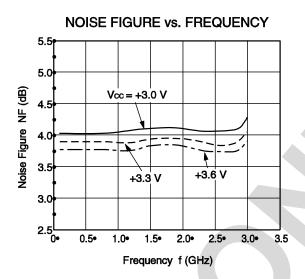
**OUTPUT POWER vs. INPUT POWER** 

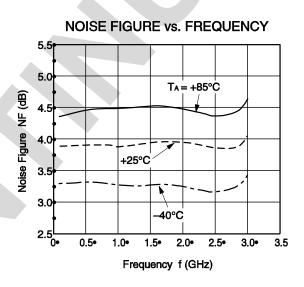


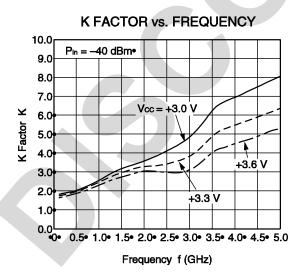
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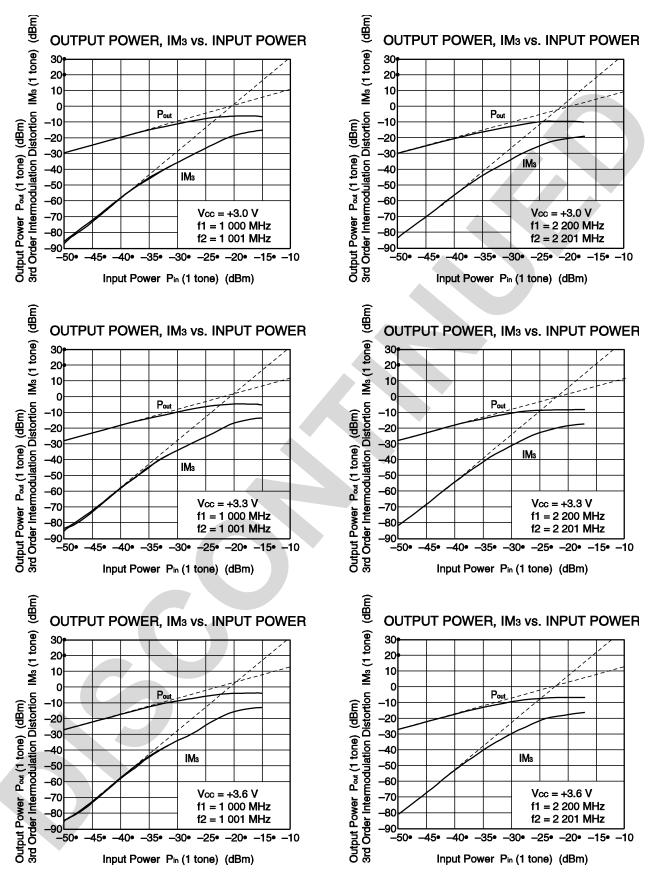




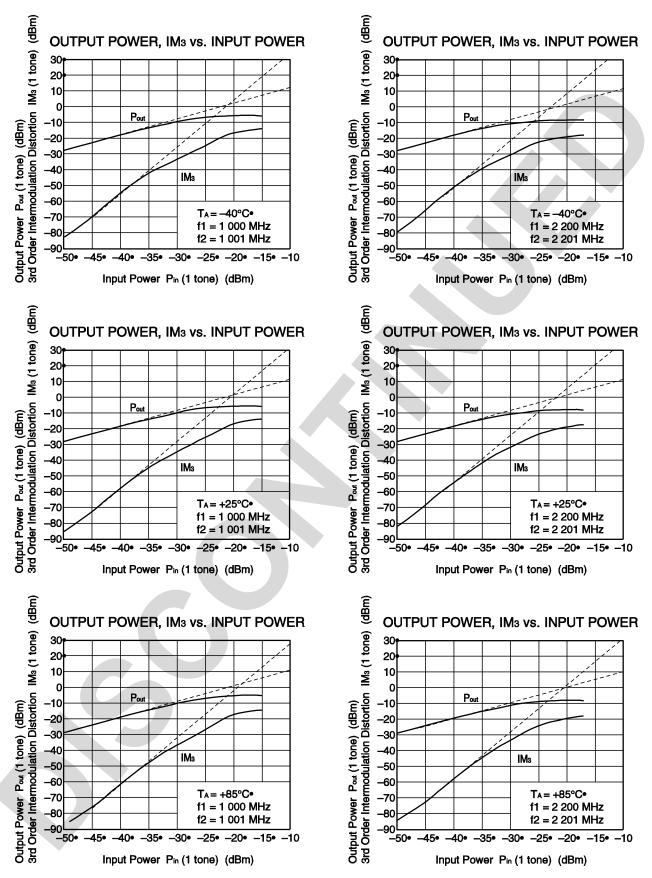




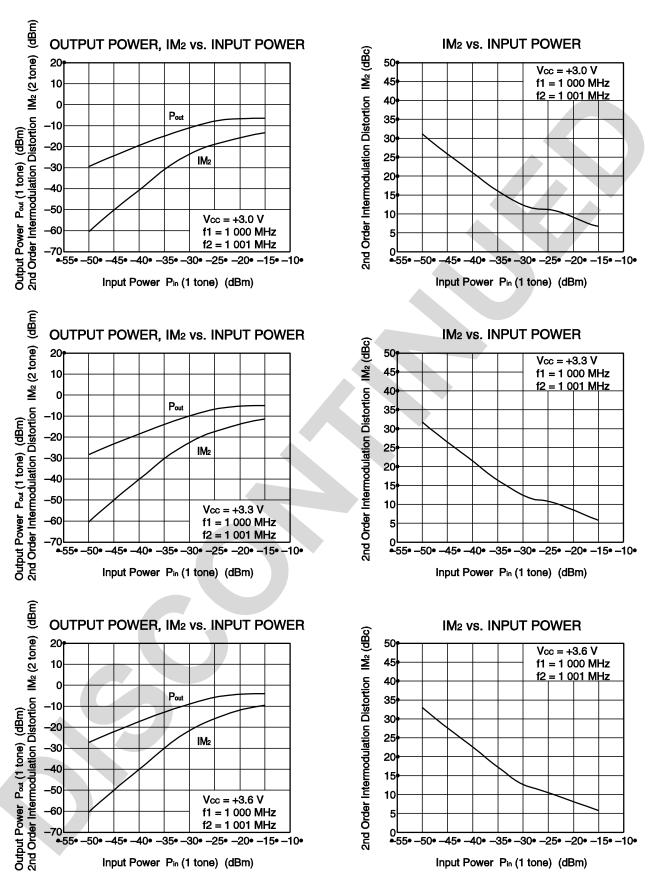
**Remark** The graphs indicate nominal characteristics.



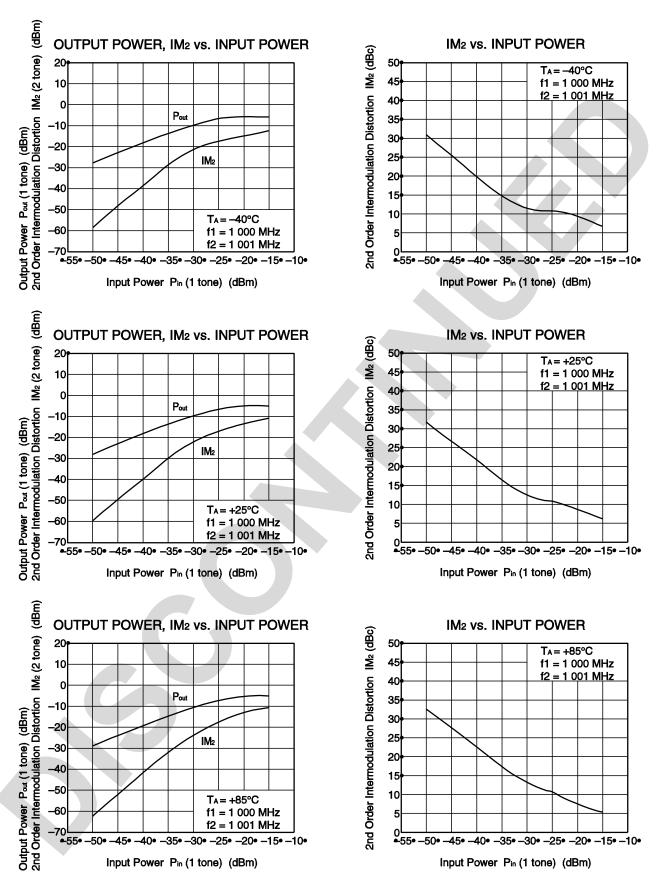
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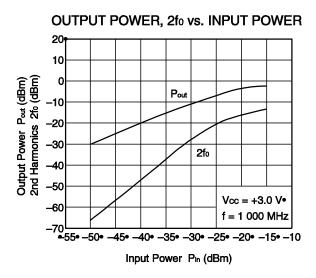
**Remark** The graphs indicate nominal characteristics.

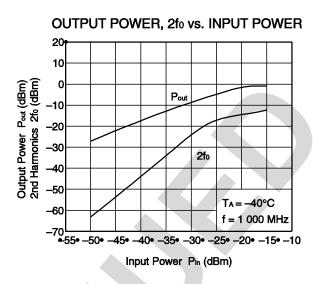


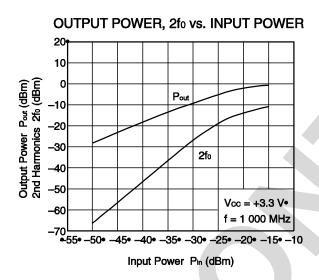
**Remark** The graphs indicate nominal characteristics.

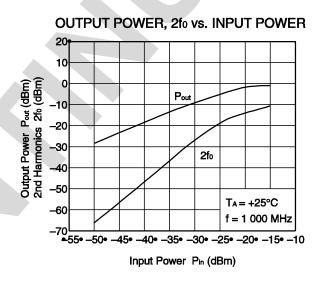


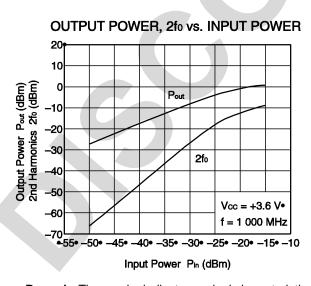
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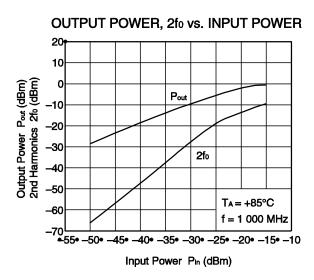








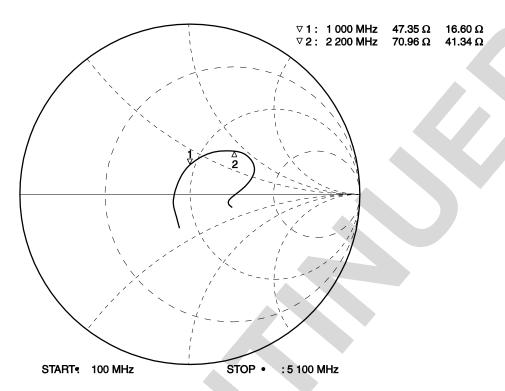




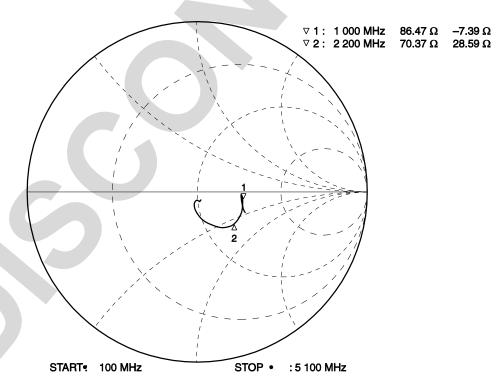
 $\label{lem:remark} \textbf{Remark} \ \ \textbf{The graphs indicate nominal characteristics}.$ 

#### S-PARAMETERS (TA = +25°C, Vcc = 3.3 V, Pin = -40 dBm)

#### S<sub>11</sub>-FREQUENCY



#### S<sub>22</sub>-FREQUENCY



Remarks 1. Measured on the test circuit of evaluation board.

2. The graphs indicate nominal characteristics.

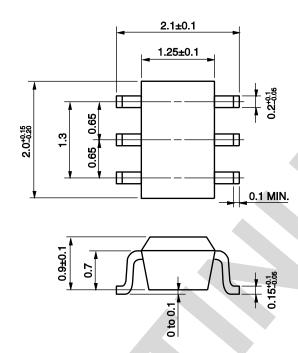
#### **S-PARAMETERS**

- S-parameters and noise parameters are provided on our Web site in a format (S2P) that enables the direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.
- · Click here to download S-parameters.
- [RF and Microwave] ® [Device Parameters]
- URL http://www.necel.com/microwave/en/



#### PACKAGE DIMENSIONS

### 6-PIN SUPER MINIMOLD (UNIT: mm)



#### NOTES ON CORRECT USE

- (1) Observe precautions for handling because of electro-static sensitive devices.
- (2) Form a ground pattern as widely as possible to minimize ground impedance (to prevent undesired oscillation).

  All the ground terminals must be connected together with wide ground pattern to decrease impedance difference.
- (3) The bypass capacitor should be attached to the Vcc line.
- (4) The DC cut capacitor must be attached to input and output pin.

#### RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions		Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) Time at peak temperature Time at temperature of 220°C or higher Preheating time at 120 to 180°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 60 seconds or less : 120±30 seconds : 3 times : 0.2%(Wt.) or below	IR260
Wave Soldering	Peak temperature (molten solder temperature) Time at peak temperature Preheating temperature (package surface temperature) Maximum number of flow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 120°C or below : 1 time : 0.2%(Wt.) or below	W\$260
Partial Heating	Peak temperature (terminal temperature) Soldering time (per side of device) Maximum chlorine content of rosin flux (% mass)	: 350°C or below : 3 seconds or less : 0.2%(Wt.) or below	HS350

Caution Do not use different soldering methods together (except for partial heating).